## **EEE109 Assignment 2**

- 1. The parameters of the MOSFET in the circuit shown in Figure 1. Parameters are  $V_{TN}=0.8~{
  m V}, K_n=0.85~{
  m mA/V^2},$  and  $\lambda=0.02~{
  m V^{-1}}$ 
  - (a) Determine  $R_S$  and  $R_D$  such that  $I_{DQ}=0.1~\mathrm{mA}$  and  $V_{DSQ}=5.5~\mathrm{V}$  [10 marks]
  - (b) Find the small-signal transistor parameters  $g_m$ , and  $r_o$ . [6 marks]
  - (c) Draw the small-signal equivalent circuit [6 marks]
  - (d) Determine the small-signal voltage gain. [8 marks]

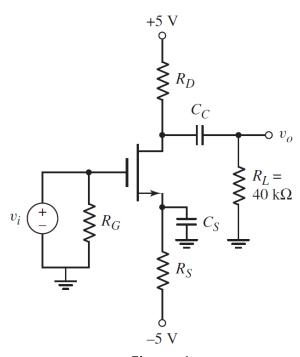


Figure 1

- 2. Consider the circuit show in Figure 2. The transistor parameters are  $\beta=100$ and  $V_A = 100$  V. Assume  $V_{BE}(\text{on}) = 0.7$  V and  $V_T = 0.026$  V.
  - (a) Determine  $I_{CQ}$  and  $V_{CEQ}$ .

[12 marks]

(b) Draw the small-signal equivalent circuit.

[4 marks]

(c) Determine the input resistance  $R_i$ 

[5 marks]

(d) Determine the small-signal voltage gain  $A_{\nu}$ 

[9 marks]

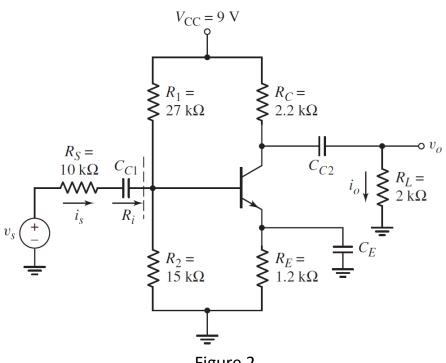


Figure 2

- 3. For the circuit in Figure 3, the transistor parameters are  $\beta=120$ ,  $V_{BE}(\text{on})=0.7$  V, and  $V_A=50$  V. Let  $R_{TH}=0.1(1+\beta)R_E$ .
  - (a) Design a bias-stable circuit such that  $I_{EQ}=1.5~\mathrm{mA}$  [10 marks]
  - (b) Using the results of part (a), find the small-signal mid-band voltage gain

[14 marks]

(c) Determine the output resistance  $R_o$ 

[10 marks]

(d) What is the lower 3 dB corner frequency?

[6 marks]

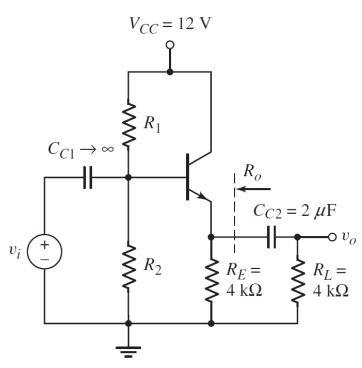


Figure 3